Electronic Supplementary Material (ESI) for RSC Advances.

Supporting information

Patterning of Amorphous-InGaZnO Thin-Film Transistors by Stamping of Surface-Modified Polydimethylsiloxane

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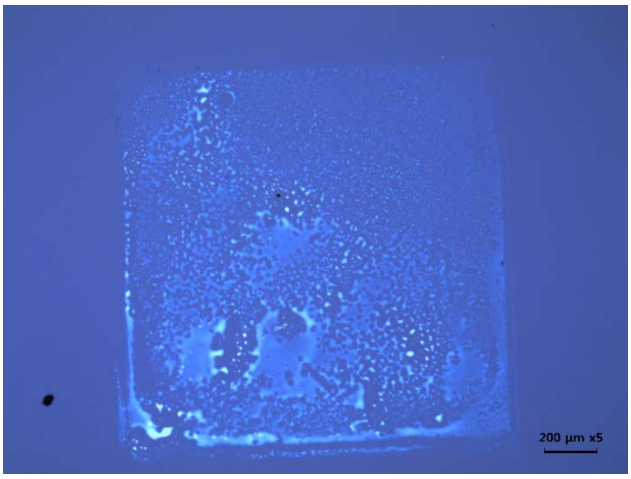

Fig. S1 Transferred IGZO layer on SiO_2/Si substrate. The PDMS stamp was not treated with piranha solution and UV-ozone.

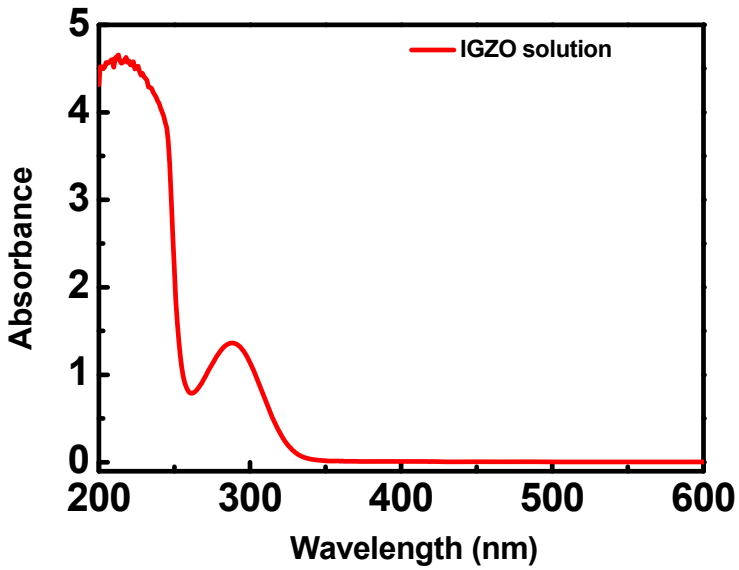

Fig. S2 Optical absorbance of IGZO solution.

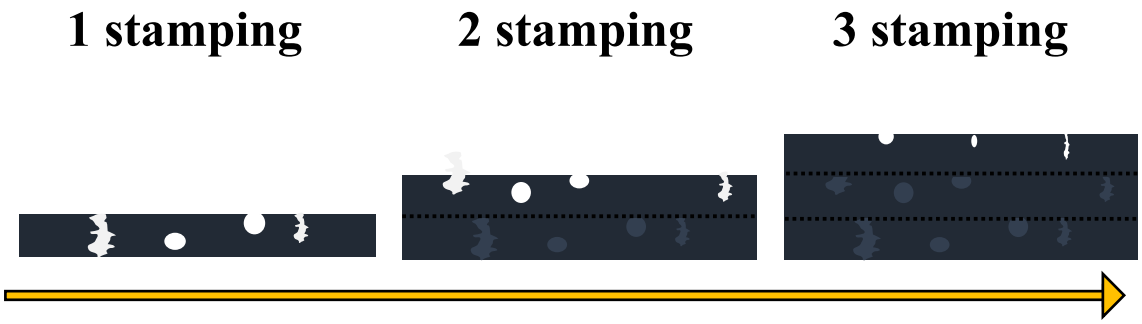

Fig. S3 Schematic illustration to show passivation of stamped layer by subsequent stamping process.

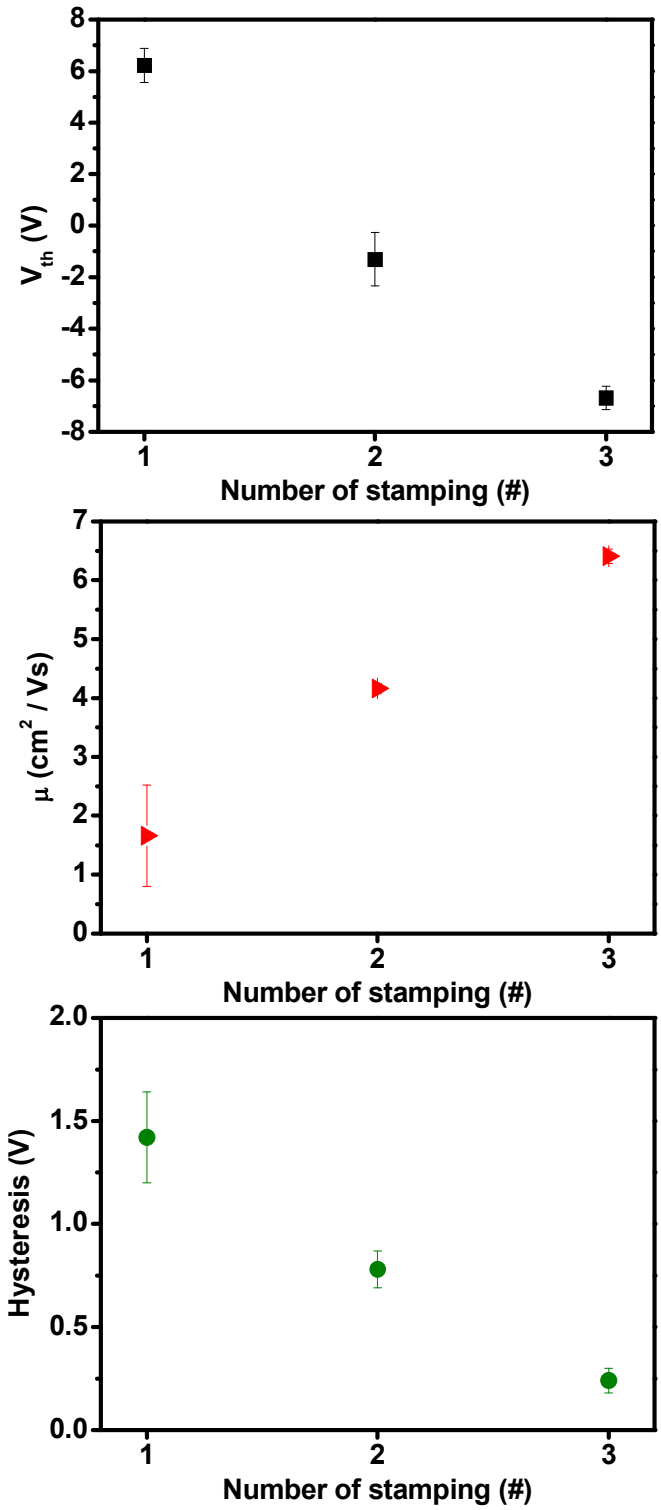

Fig. S4 The changes in electrical properties of stamped IGZO TFTs with the number of stamping layers.